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The e ect of surface roughness on the structure of liquid crystalline uids near solid substrates is studied by M onte C arlo simulations. The liquid crystal is modelled as a uid of soft ellipsoidal molecules and the substrate is modelled as a hard wall that excludes the centres of m ass of the

uid molecules. Surface roughness is introduced by embedding a number of molecules with random positions and orientations within the wall. It is found that the density and order near the wall are reduced as the wall becomes rougher (i.e. the number of embedded molecules is increased). Anchoring coe cients are determined from uctuations in the reciprocal space order tensor. It is found that the anchoring strength decreases with increasing surface roughness.

I. IN TRODUCTION

The interaction between liquid crystalline (LC) uids and solid surfaces has attracted much interest¹. The presence of the surface breaks the symmetry of the LC phase. As well as being intrinsically interesting this is technologically important - m any applications of liquid crystals depend on the interaction between the uid and an external eld, strongly in uenced by coupling with external surfaces.

Most previous studies of LC surface andhoring have assumed that the surface is hom openous. Two models are commonly used. In the st the wall is modelled by a perfect crystalline array². The second, more coarse grained model, uses an external potential function that depends only on the distance from the wall^{3,4}. W hile attractive from a theoretical standpoint, it has long been recognised that deviations from these ideal surfaces can a ect the properties of the surface⁵. One notable example of this is the reduction of the order parameter of nem atic liquid crystals at SiO surfaces^{6,7}. This contrasts with m easurements m ade on other surfaces 1 (e.g. rubbed polyim ide) and with most simulation and theoretical studies that give a higher order param eter at the LC-solid interface. Electron m icrographs show that SiD surfaces are extremely rough⁸, which gives rise to the disordering e ect of the surface.

In this paper the structures of nem atic and isotropic uids near rough walls are studied. The e ect of roughness is incorporated by embedding a number of molecules in an otherwise smooth wall. These are placed and orientated random ly. Sim ilar models have been used for simple uids^{9,10} and it is hoped that this simple model may give insights into the behaviour of molecular uids near rough or porous surfaces. Two aspects of the effect of the surface roughness on the LC uid are studied. Firstly the change in the structure of the uid was exam ined. Secondly the e ect of surface roughness on the anchoring properties of the LC. The contribution of this surface anchoring to the free energy is often taken to be of the Rapini-Popoular form $^{11}\,$

$$F_{surf} = W \sin^2 (0)$$
 (1)

where ₀ is the angle between the director at the surface and the surface's 'easy-axis'. W is the surface andhoring coe cient. This depends on both the properties of the bulk liquid crystal and on the interaction between the liquid crystal and the surface, so may be expected to vary with surface roughness. As this is a key property in applications of liquid crystals it would be interesting to see how this is a ected by changes in the surface m orphology.

This paper is organised as follows. Details of the simulation, including the method used for calculating the anchoring coe cient, are given in the next section. The structure of the uid con ned between rough walls is given in Sec. III while results for the anchoring coe cient are presented in Sec. IV. Finally some concluding remarks are given in Sec. V.

II. SIM ULATION

A. Simulated Systems

In order to simulate large system s, a simple interm olecular potential is used. This models the uid as a system of soft ellipsoidalm olecules interacting through a simplied version of the popular G ay-Berne (GB) potential¹². In particular this has two major simplications. First the orientation dependence of the energy parameter is suppressed. Secondly the potential is cut o and shifted at the potential minima. These changes lead to a much simplier phase diagram than the GB potential, showing only nem atic and isotropic phases, closer to the phase behaviour of the hard ellipsoid¹³ or hard gaussian overlap¹⁴ potentials. This potential is also more computationally e cient than the full GB potential.

The interaction between two molecules i and j, with positions $r_{\rm i}$ and $r_{\rm j}$, and orientations $u_{\rm i}$ and $u_{\rm j}$ is given by

$$V(\mathbf{r}_{ij};\mathbf{u}_{i};\mathbf{u}_{j}) = \begin{array}{ccc} 4_{0} & {}^{12} & {}^{6} + 1; & 2^{1=6} \\ 0 & ; & \text{otherw ise} \end{array}$$
(2)

P resent address: D ept. of P hysics, U niversity of W arw ick, C oventry, C V 4 7A L, U K

where $_0$ is the energy unit, $r_{ij} = r_i - r_j$, and

$$(\mathbf{r}_{ij}; \mathbf{u}_{i}; \mathbf{u}_{j}) = \frac{\mathbf{r}_{ij}}{0} \qquad (\mathbf{r}_{ij}; \mathbf{u}_{i}; \mathbf{u}_{j}) + \mathbf{u}_{0} = \mathbf{u}_{0} \qquad (3)$$

 $r_{ij} = jr_{ij}j r_{ij} = r_{ij}=r_{ij}$, and $_0$ is the $(r_{ij};u_i;u_j)$ is the shape function given by¹⁵

$$\begin{pmatrix} \hat{\mathbf{r}}_{ij}; \mathbf{u}_{i}; \mathbf{u}_{j} \end{pmatrix} = {}_{0} 1 \frac{2}{2} \frac{(\hat{\mathbf{r}}_{ij} \mathbf{u}_{i} + \hat{\mathbf{r}}_{ij} \mathbf{u}_{j})^{2}}{1 + \mathbf{u}_{i} \mathbf{u}_{j}} + \frac{(\hat{\mathbf{r}}_{ij} \mathbf{u}_{i} + \hat{\mathbf{r}}_{ij} \mathbf{u}_{j})^{2}}{1 + \mathbf{u}_{i} \mathbf{u}_{j}} = (4)$$

This approximates the contact distance between two ellipsoids. In Eq. 4 = $\binom{2}{1} = \binom{2}{2} + 1$ is the anisotropy parameter, where is the elongation (for the molecules studied here = 3).

The wall is represented by a hard core potential acting upon the centres of mass of the molecules. P revious studies have shown that this gives rise to hom eotropic alignment at the wall¹⁶. Roughness is introduced by embedding a number of molecules, N $_{\rm w}\,$ in the wall. These were given random positions and orientations which were kept xed during the sim ulations. W hile generating these surface con gurations interactions between the surface m olecules were ignored, thus these m olecules m ay overlap. It should be noted that these molecules do not correspond to realm olecules, rather they are used as a convient way of introducing inhom ogenity into the wall. The roughness of the wall was characterised by the surface density of these embedded molecules = $N_w = A$. Som e example wall structures are shown in Fig. 1. To ensure som e sam pling of surface con gurations three di erent surfaces were studied for each pair of and .

Simulations were performed at two average densities, = 0.314 and = 0.30. For the higher density the uid conned between smooth walls was nematic, while it is isotropic for the lower density. The simulated systems were composed of 1200 uid molecules and up to 63 molecules embedded in each wall. Throughout this reduced units de ned by the molecular width $_0$ and the energy unit $_0$ are used. A reduced temperature of 0.5 was used for both densities.

B. Simulation observables

The orientational order m ay be characterised by the usual nem atic order parameter. This is given by the largest eigenvalue of the ordering tensor, de ned as

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$$Q = \frac{1}{N} \sum_{i=1}^{N} \frac{3}{2} u_i u_i = \frac{1}{2} ; ; = x;y;z$$
(5)

where u_i is the orientation of the ith molecule and is the K ronecker delta function. It may also be informative to consider the order parameter in the cell bulk (a)

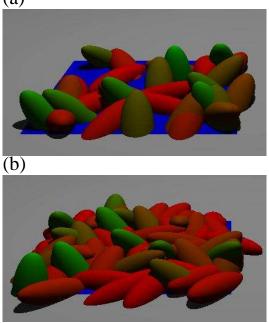


FIG.1: (Color online) Example rough wall con gurations for (a) = 0.2 and (b) = 0.4.

and near the surface, S^{bulk} and S^{surf} . S^{bulk} is calculated form olecules within the region $l_z=4$ z $3l_z=4$, while S^{surf} is calculated form olecules within 1 $_0$ of the surface.

The distribution of molecules in the simulation cell can be described by the density prole (z). To describe the ordering through the cell, the ordering tensor Eq. 5 can be calculated throughout the cell. D iagonalising this gives the order parameter proles (q_t (z), q_D(z), and q (z)). These can be expressed as S (z), S (z) + $\frac{1}{2}S_{xy}$ (z), and S (z) $\frac{1}{2}S_{xy}$ (z), where S (z) is the nem atic order parameter and S_{xy} (z) is the biaxiality parameter.

The nem atic director n (z) can be identied with the eigenvector of the ordering tensor corresponding to the largest eigenvalue.

W hile the presence of layers may be deduced from the density proles it may be useful to quantify the degree of translational order. The sm ectic order parameter may be introduced for this $puppose^{17,18}$. This is given by

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$$I_{1} = \frac{1}{N} \frac{X^{N}}{\sum_{j=1}^{j}} \exp \frac{2 i z_{j}}{d} ; \qquad (6)$$

where d is the layer periodicity. This is initially unknown and is take to be the value that maxim ises 1^{18} .

C. Director uctuations and surface anchoring

The surface anchoring \cos cient is determ ined by the director uctuation method^{19,20}. This method relates

therm all director uctuations in a conned geometry to the zenithal anchoring coecient, in a similar manner as the uctuations in a bulk LC can be related to the bulk elastic constants^{21,22}. The theory for this has been extensively developed elsewhere and this section will contain only the briefest of outlines.

As for the bulk elastic constants the zenithal anchoring coe cient may be determined by thing elastic theory predictions of uctuations in the ordering tensor to those determined from simulations. The reciprocal space ordering tensor is given by

$$Q \quad (k) = \frac{V}{N} \sum_{i}^{X} Q^{i} \exp(ik \mathbf{r}_{i}) :$$
 (7)

Fluctuations can be calculated from simulation

The corresponding elastic theory predicts that there uctuations are given by¹⁹

$$D_{12} (k_{z})^{2}_{J} = \frac{9}{8} k_{B} T \frac{S^{2}V}{K_{33}} X_{q_{z}} \frac{2+2}{q_{z}^{2}(2+2+2)}$$
$$\frac{e^{i(+)}1}{+} + \frac{i}{i+} \frac{e^{i(-)}1}{2}$$
(9)

where K_{33} is the bend elastic constant. q_z is a wave vector with a discrete spectrum¹⁹, = $q_z L_e$, and = $k_z L_e$. is the anchoring strength parameter

$$=\frac{W L_e}{K_{33}} = \frac{L_e}{(10)}$$

where W is the zenithal anchoring coe cient and is the extrapolation length. L_e is the cell thickness appearing in the elastic theory; this is not necessarily equal to the simulation cell thickness, L_z . In thing the elastic theory to simulation pro les L_e and are the thing parameters. K₃₃ has been determined from simulation for a nearby state point²³ (= 0.30). W hile this value (K₃₃ = 1:48) is likely to be too large for some of the system s studied here, this should be su cient for a qualitative study.

III. FLUID STRUCTURE

A. High Density Fluid

The density pro les for the high density uid are shown in Fig. 2a. The e ect of the wall roughness is most apparent near the wall. Here the density near the surface

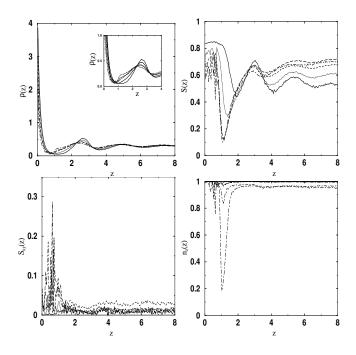


FIG.2: (a) Density pro les for the high density uid near rough walls. The density pro le for grafting density = 0 is shown by the solid line, for = 0:1 dotted line, = 0:2 dashed line, = 0:3 long dashed line, and = 0:4 the dashed dotted line. Inset shows the density pro les around the minima. Symbols as in main gure.

(b) Order parameter pro les for high density uid near rough walls. Symbols as in (a).

(c) Biaxiality (S_{xy}) profes for high density uid near rough wall. Symbols as in (a).

(d) z component of the director for the high density uid. Symbols as in (a). $3 n_z$ (z) pro les are shown for = 0.4.

decreases with increasing . This is caused by the decrease in available volume near the wall due to the embedded molecules. Values of the density near the wall are presented in Tab. 1. The surface density falls from 0.72 for the sm ooth wall to 0.34 for the rough wall with = 0.4.

A nother noticeable di erence is that the second peak (at z = 2.8 for the plain wall) becomes broader. This arises from the surface disorder disturbing the layer structure and has been observed in simulations of Lennard-Jones uids¹⁰. This can more clearly be seen in the inset, which shows the detail of the density proles around the minim a. The disruption of the translational ordering caused by the embedded molecules can be seen by considering the smectic order parameter (Eq. 6). Values for these are presented in Tab. 1. As can be seen $_1$ markedly decreases with increasing grafting density, as would be expected for increasing translational disorder.

Far from the wall the proles all tend to a constant values, indicating a layer of bulk uid. The density of this layer increases slightly with increasing grafting density. This arises as the embedded molecules exclude uid molecules from regions near the wall, increasing the num - ber of m olecules in the cell bulk. This is a consequence of having a xed cell size and may be avoided by using N pT simulations. Quantitively this can be seen by examining the densities in the cellbulk. Values for this are presented in Tab. 1. The density in the bulk of the cell goes from 0.29 for the sm ooth wall to 0.31 for the highest grafting densities.

Figure 2 (b) shows the order parameter proles for different values of . As can be seen the value of the order parameter at the wall is lower for higher grafting densities. This is caused by the disorientating e ect of the embedded molecules. This disorientating e ect also leads to a deeper minima. For 0.2 this leads to a small layer (approximately 1 molecular width thick) of almost isotropic uid. The position of this minima m oves closer to the wall with increasing surface roughness. For the smooth wall this minima is at approxim ately z = 2, while for the highest grafting densities it appears at about z = 1:1. Again this is attributable to the disruption in the surface induced layering. As for

(z) the second peak becomes broader with increasing . Finally, as can be seen from Tab. 1 the bulk order parameter S^{bulk} increases with increasing . This is a consequence of the increasing density in the centre of the cell due to the excluded volume e ect of the embedded molecules. It is noticeable that for 0.2 S^{bulk} becomes larger than S^{surf}.

The biaxiality projes are shown in Fig. 2 (c). For the smooth wall the this is essentially zero (the largest value is 0.04) rejecting the cylindrical symmetry around the z axis. However, for the rough walls there is are sizable peaks in the biaxiality projes. These are stronger for larger values of and are in the region of 0.5 z 1:3, corresponding to regions of low order. This surface induced biaxiality has been seen for simulations of LCs near grooved surfaces²⁴.

Table 1.

D ensities and order parameters for the simulated system s. _{bulk} and _{surf} are the bulk and surface densities, S, S^{bulk} and S^{surf} are the total, bulk and surface order parameters, and ₁ is the smectic order parameter. Errors in the last decimal place are in parenthesizes.

		surf	bu lk	S	S^{surf}	S^{bulk}	1
0.314	0	0.72(1)	0,286 (3)	0.60(3)	0.84(1)	0.53(6)	0.14(2)
0.314	0.1	0.61(1)	0,294 (2)	0.64 (2)	0.76(2)	0.65(3)	0.12(2)
0.314	02	0.48(3)	0.304 (3)	0.67(2)	0.65(3)	0.72(2)	0.10(2)
0.314	0.3	0.43(5)	0.308(4)	0.69(2)	0.65 (9)	0.75(2)	0.09(2)
0.314	0.4	0.33(2)	0.307 (9)	0.66 (8)	0.58(7)	0.73(7)	0.07(2)
0.300	0	0.70(1)	0,273(2)	0,28 (3)	0.81(1)	0.10(4)	0.14(2)
0.300	0.1	0.59(1)	0,281(2)	0.34(7)	0.72(3)	0,27 (9)	0.12(2)
0.300	0.2	0.46(2)	0,291 (3)	0.52 (6)	0.61(3)	0.59(5)	0.10(2)
0.300	0.3	0.41(2)	0,293 (3)	0.51(4)	0.53 (9)	0.60(4)	0.09(2)
0.300	0.4	0.38(1)	0.300(3)	0.59(6)	0.54(5)	0.69(3)	0.07(2)

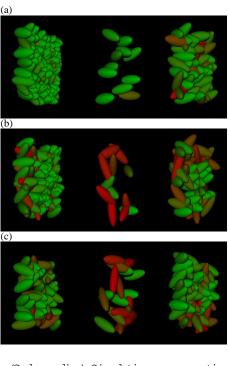


FIG. 3: (Color online) Simulation con gurations showing molecules within 2.5 $_0$ of the surface for (a) = 0, (b) = 0.2, and (c) = 0.4. For each the left most picture shows molecules with 0 z 0.5, the centre pictures shows 0.5 z 1.5, and the right most shows 1.5 z 2.5.

Figure 2 (d) shows the z component of the director for each . In the cellbulk the director is essentially parallel to the z axis. For 02 there is a tilt away from the z axis at about the position of the order minima. As m ay be expected this is most pronounced for the = 0:4wall. In Fig. 2d the pro les for each of the = 0.4 walls are shown separately. It can be seen that the size of this tilt di ers strongly for di erent wall con gurations (for the largest the tile angle is approxim ately 79). For the larger tilt angles this propagates into the bulk of the uid leading to a director tilted up to 16 from the z-axis. It is not clear how a random ly generated wall gives rise to a titled con guration in the bulk. Sim ilar behaviour has been seen in a recent study of a LC near a planar wall with perpendicularly grafted $rods^{25}$. In that case the bulk tilt was caused by the competition between the wall (which promoted planar alignment) and the embedded molecules. As it appears only for a subset of the walls studied here it would be desirable to consider further wall con qurations.

The previous discussion m ay be illum inated by exam ination of simulation con gurations. Figure 3 shows congurations of for = 0.0 (sm ooth wall), = 0.2, and = 0.4. The disordering e ect of the rough wall can be seen in the rst and second layers (left and right m ost pictures). However, the uid between these two layers shows the most noticeable change with increasing . For the sm ooth wall the m olecules in this region are still well

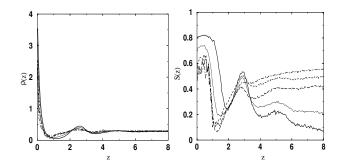


FIG. 4: (a) Density proles for the low density uid near rough walls. The density prole for grafting density = 0 is shown by the solid line, for = 0:1 dotted line, = 0:2 dashed line, = 0:3 long dashed line, and = 0:4 the dashed dotted line.

(b) Order parameter pro les for the low density uid. Symbols as in (a).

ordered parallel to the z-axis. W ith increasing the m olecules in this region become increasingly disordered. This gives rise to the deeperm inim a seen in the order parameter pro le (Fig. 2(b)). Additionally it can be seen that m any of the molecules lie in the xy plane, giving rise to the biaxiality peak and the tilt of the director away from the z axis. This behaviour is similar to that seen in simulations of sm ectic liquid crystals²⁶ where molecules in the region between the layers are seen to align either parallel or norm al to the layers. These planar oriented molecules possibly give rise to the bulk tilt seen in some cases. Finally the number of molecules in this region visibly increases with .

B. Low Density Fluid

Here the density and order parameter proles for the low density system are discussed. For the smooth wall the density in the bulk of the cell is 0.27 (Tab. 1), just below the isotropic-nem atic transition density for this system ($_{\rm IN} = 0.287$). As the density in the cell bulk increases with , for 0.2 the uid in the cell bulk is nem atic rather than isotropic.

The density proles for the low density uid are shown in Fig. 4(a). The changes in the density prole with increasing are similar to those in the high density system -the density at contact decreases with and the second peak becomes more diluse. Again this can be gleaned from the decrease in the value of the smectric order parameter with (Tab. 1). It is interesting to note that the values of $_1$ obtained in this system are very similar to those for the higher density system, indicating the similarity in the structure of both system s.

Shown in Fig. 4 (b) are the order parameter proles. As in the high density uid the value of the order parameter at the wall decreases as increases. The order parameter prole also shows a deeper minima with increasing surface roughness. It is noticeable that even in

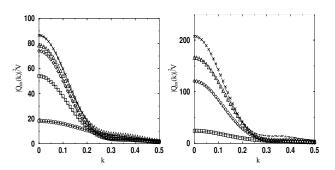


FIG.5: Order tensor uctuations (normalised by cell volume) as a function of wavevector for (a) high density and (b) low density uids. In both graphs the simulation data is denoted by symbols (circles = 0, squares = 0:1, diam onds = 0:2, triangles = 0:3, and crosses = 0:4) and the elastic theory data is shown by lines (continuous line = 0, dotted line = 0:1, dashed line = 0:2, long dashed line = 0:3, and dot dashed line = 0:4). The order tensor uctuations for = 0:0 are shown only in (a).

this lower density case there is not an appreciable layer of isotropic uid between the wall and bulk uid. This has been predicted to happen near rough walls as a consequence of the competition between the bulk director and the local boundary conditions²⁷.

IV. SURFACE ANCHORING

Shown in Fig. 5 are the order tensor uctuations as a function of wavevector. As can be there is good agreement between the simulation and elastic theory curves, especially for small $k_{\rm z}$.

The tted values for the anchoring coe cients are given in Tab. 2 along with values of the extrapolation length and the surface anchoring coe cient W. For both bulk densities tends to decrease with increasing

Table 2.

Fitting data for the order tensor uctuations (Fig. 5). is the anchoring coe cient, and L $_{\rm e}$ is the elastic theory cellwidth, which appear in Eq. 9. = L $_{\rm e}$ = is the extrapolation length and W = K $_{33}$ = is the surface

anchoring strength.

			Le		W
0.314	0.0	5.62	16.00	2.85	0.52
0.314	0.1	6.51	28.39	4.36	0.34
0.314	0.2	5.64	29.36	5.21	0.28
0.314	0.3	4.94	26.80	5.43	0.27
0.314	0.4	4.55	27.78	6.11	0.24
0.30	0.1	3.05	18.32	6.01	0.24
0.30	0.2	2.88	24.60	8.54	0.17
0.30	0.3	2.58	23.85	9.24	0.16
0.30	0.4	2.70	25.44	9.42	0.16

The behaviour of the elastic theory cellwidth, L_e , with deserves comment. For the high density uid, L_e for the smooth wall is 16.00 $_0$, a few molecular lengths smaller than the physical cell width ($L_z = 24.66$). This is similar to behaviour seen in previous simulations^{19,20} and is due to the formation of highly ordered layers in the vicinity of the surface. For the rough walls how ever, L_e is larger than L_z . This increase may be attributable to the rough surface breaking up the highly ordered surface layer. Thus instead of the elastic theory boundary conditions being applied at this layer, they are applied closer to the wall, leading to an increase in L_e .

For both bulk densities the extrapolation length increases and the anchoring coe cient W decreases with . Thus, as may be intuitively expected, anchoring on rough surfaces is weaker than on sm ooth surfaces.

V. SUMMARY

In this paper results of M onte C arlo simulations for a conned uid of ellipsoidal molecules have been performed. The e ect of surface roughness on the structure of the uid has been examined. Roughness was introduced by embedding a number of molecules, with random positions and orientations, in otherwise smooth walls. Increasing the number of molecules embedded in the wall corresponds to an increasing surface roughness. The simulations were performed at two bulk densities. For the higher density the uid in the bulk of the cell is nem atic for the smooth wall case, while for the lower density it is isotropic.

At both densities studied the e ect of increasing surface roughness is similar. Both the density and order parameter in the region near the wall decrease as the num ber of em bedded m olecules increases. The decrease in the density arises from the excluded volume of the em bedded m olecules, while the decrease in the order can be attributed to the disorientating e ect of the random ly orientated m olecules in the wall. The rough walls also act to sm ear out the secondary peaks in the density and order parameter pro les as the em bedded m olecules give anchoring points at positions other than at the wall surface. One side e ect of the wall roughness is an increase in the density and order parameter in the centre of the cell.

A los studied was the e ect of surface roughness on the surface anchoring strength. For both systems the anchoring was found to become progressively weaker with increasing surface roughness.

A number of possible avenues for future work are possible. Calculation of the anchoring coe cient via alternative m ethods^{16,28} would be useful. As the formation of a highly ordered layer at the surface is commonly held to be important for the growth of order in conned liquid crystals, it may be interesting to investigate the elect of wall roughness on the phase behaviour of the conned uid¹⁷. Integral equation²⁹ or density function theories³⁰ have been applied to similar systems of simple uids and appropriate generalisations to molecular uids should also prove useful.

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